

In the Specification:

At the beginning of the specification, please enter the following paragraph:

– This application is a divisional of co-pending U.S. Patent Application Serial No. 09/970,785 filed on October 5, 2001, which has now become U.S. Patent No. _____. –

In the Claims:

Please cancel claims 1-2 without any disclaimer or a prejudice.

Please amend claim 3 as follows:

1. (Cancelled)

2. (Cancelled)

3. (Currently Amended) A thin film transistor substrate, comprising:
a gate wiring formed on an insulation substrate that includes gate lines, and gate
electrodes and gate pads connected to the gate lines;
a gate insulation layer covering the gate wiring;
a semiconductor layer formed over the gate insulation layer;
a data wiring formed over the gate insulation layer that includes data pads;
a protection layer covering the data wiring;
auxiliary pads connected to the data pads through contact holes formed in the protection
layer; and

a pad auxiliary layer formed protruding a predetermined height under the data pads ~~The thin film transistor substrate of claim 1~~, wherein the pad auxiliary layer is formed on a same layer as the gate wiring.

4. (Original) The thin film transistor substrate of claim 3, wherein the data wiring further includes data lines, source electrodes connected to the data lines, and drain electrodes provided opposing the source electrodes with respect to the gate electrodes.

5. (Currently Amended) The thin film transistor substrate of claim 4, further comprising a pixel electrodes formed on a same layer as the auxiliary pads and connected to the drain electrodes.

6. (Original) The thin film transistor substrate of claim 5, further comprising an ohmic contact layer formed between the semiconductor layer and the data wiring, the ohmic contact layer being doped with impurities at a high concentration.

7. (Currently Amended) The thin film transistor substrate of claim 6, wherein the ohmic contact layer is formed in the same shape as the data wiring.

8. (Original) The thin film transistor substrate of claim 7, wherein the semiconductor layer, except for a channel formed between the source electrodes and the drain electrodes, is formed in the same shape as the data wiring.

9. (Original) The thin film transistor substrate of claim 8, wherein the pad auxiliary layer is made of an aluminum group conducting material, the auxiliary pads are made of IZO, and

the pad auxiliary layer and the auxiliary pads are interconnected via the contact holes of the data pads.

10. (Currently Amended) A thin film transistor, comprising:

a gate wiring formed on an insulation substrate and including gate lines, and gate electrodes and gate pads connected to the gate lines;

a gate insulation layer covering the gate wiring;

a semiconductor layer formed over the gate insulation layer;

a data wiring formed over the gate insulation layer and including data lines, source electrodes connected to the data lines, drain electrodes provided opposing the source electrodes with respect to the gate electrodes, and data pads connected to the data lines;

a protection layer covering the data wiring; and

a pixel electrodes connected to the drain electrodes through contact holes formed on the protection layer,

wherein the protection layer or the gate insulation layer is removed at pad portions where the data pads are formed such that at least the data pads are fully exposed.

11. (Original) The thin film transistor of claim 10, further comprising auxiliary pads formed on a same layer as the pixel electrodes and covering the data pads.

12. (Original) An inspection system for determining whether a thin film transistor substrate is defective, in which the thin film transistor substrate comprises gate wiring including gate lines, gate electrodes and gate pads, and data wiring including source electrodes and drain electrodes, the inspection system comprising: a probe pin for contacting the gate pads or data pads and transmitting a corresponding signal,

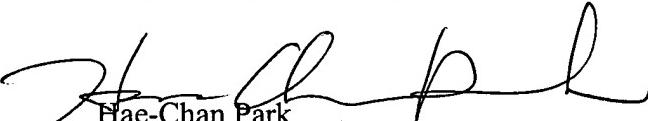
wherein a contact tip at a distal end of the probe pin for contacting the gate pads or the data pads is rounded, and a radius of the rounded contact tip is 2 μ m or less, or the rounded contact tip is coated with gold (Au).

Conclusion

By this amendment, claims 3-12 are pending in the present Application, among which claims 3, 10 and 12 are independent. It is respectfully requested that this amendment be entered prior to the examination of the above-referenced patent application. It is believed that no new matter is added by this amendment. If the Examiner desires any additional information, the Examiner is invited to contact applicants' attorney at the telephone number listed below to expedite prosecution.

Prompt and favorable consideration is respectfully requested.

Respectfully submitted,



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